

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

2SK4125 — General-Purpose Switching Device

Applications

Features

- ON-resistance RDS(on)= 0.47Ω (typ.)
- Input capacitance Ciss=1200pF (typ.)
- · 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		600	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	ID		17	А
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	52	А
Allowable Dower Dissination	action D-		2.5	W
Allowable Power Dissipation	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*1	170	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *2	EAS		78.8	mJ
Avalanche Current *3	IAV		17	А

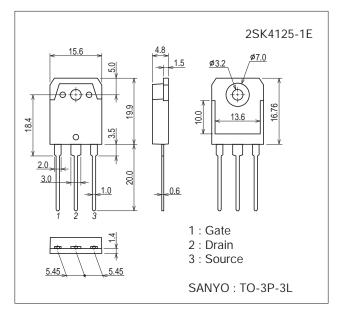
^{*1} SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- $^*2~V_{DD}\!\!=\!\!50V\!,\,L\!\!=\!\!500\mu H\!,\,I_{AV}\!\!=\!\!17A~(Fig.1)$
- *3 L≤500µH, single pulse

Package Dimensions

unit : mm (typ) 7539-002



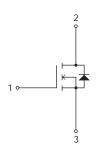
Product & Package Information

• Package: TO-3P-3L

• JEITA, JEDEC : SC-65, TO-247, SOT-199 • Minimum Packing Quantity : 30 pcs./magazine

Marking

Electrical Connection



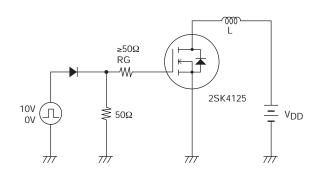
Electrical Characteristics at Ta=25°C

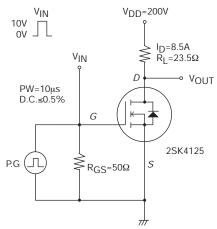
Parameter	Symbol	Conditions		Ratings	Unit		
Parameter	Symbol	Conditions	min	typ	max	UIIIL	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	600			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =480V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8.5A	4.5	9		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =7A, V _{GS} =10V		0.47	0.61	Ω	
Input Capacitance	Ciss			1200		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		220		pF	
Reverse Transfer Capacitance	Crss			50		рF	
Turn-ON Delay Time	t _d (on)			26.5		ns	
Rise Time	t _r	Con Fig 2		82		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		145		ns	
Fall Time	tf			52		ns	
Total Gate Charge	Qg			46		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =17A		8.3		nC	
Gate-to-Drain "Miller" Charge	Qgd			26.7		nC	
Diode Forward Voltage	V _{SD}	I _S =17A, V _{GS} =0V		1.0	1.3	V	

Fig.1 Avalanche Resistance Test Circuit

Fig.2 Switching Time Test Circuit

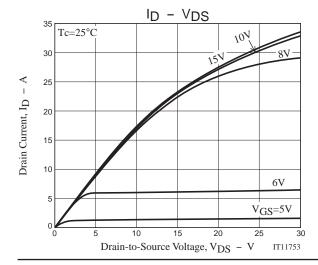
V_{IN} V_{DD}=200V

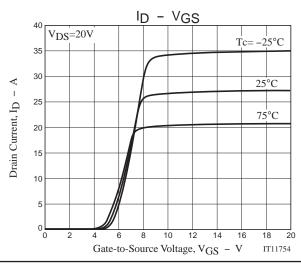


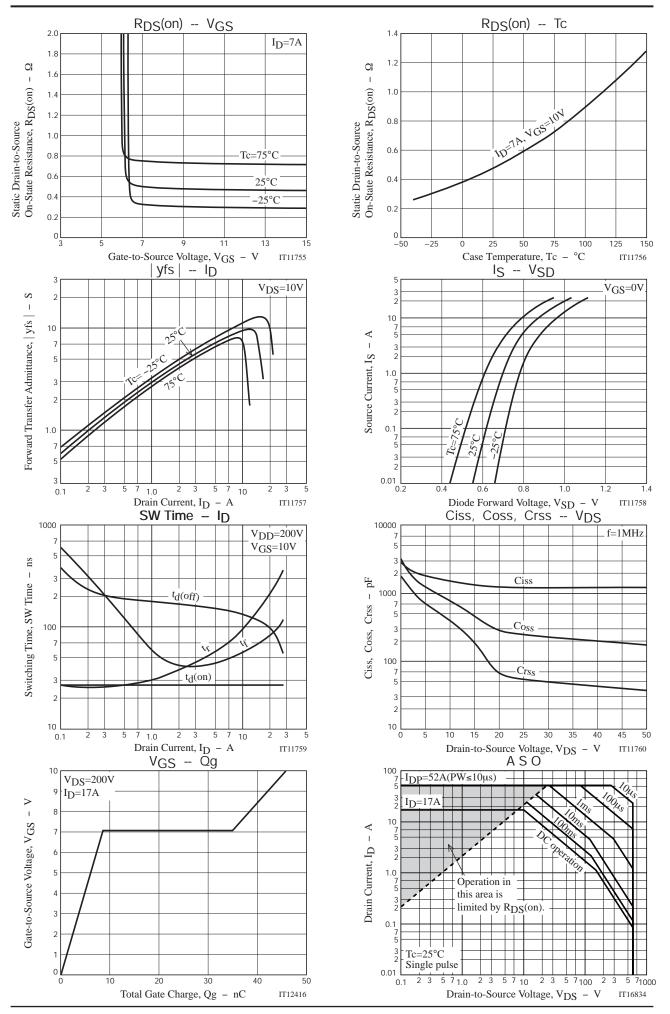


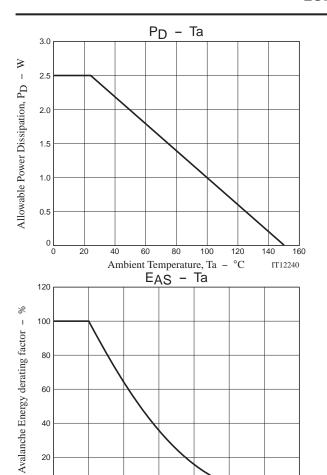
Ordering Information

Davida	Darkana	Cl. L. L.		
Device	Раскаде	Shipping	memo	
2SK4125-1E	TO-3P-3L	30pcs./magazine	Pb Free	







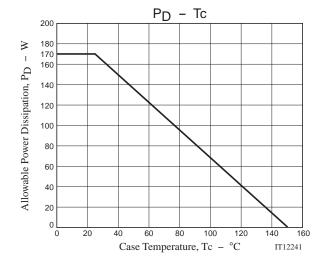


50 75 100 125 Ambient Temperature, Ta – °C

175

150 IT10478

0 0

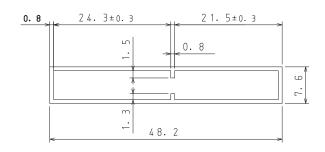


Magazine Specification

2SK4125-1E

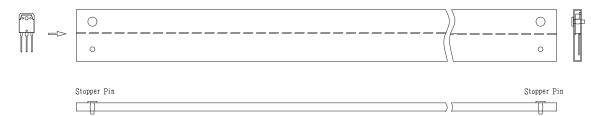
1. Packing Format

Packag	Package Name	Maximum Number of devices contained (pcs)			Packing format			
Tuonus	0 144110	Magazine	Inner box	Outer box	Inner BOX	Outer BOX		
TO-3	P-3L	30	450	1800	012 0.0001	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178		



Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

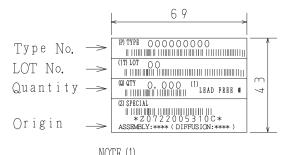
3. Storage method to magazine

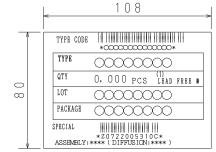


4. Inner box label (unit:mm)



It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



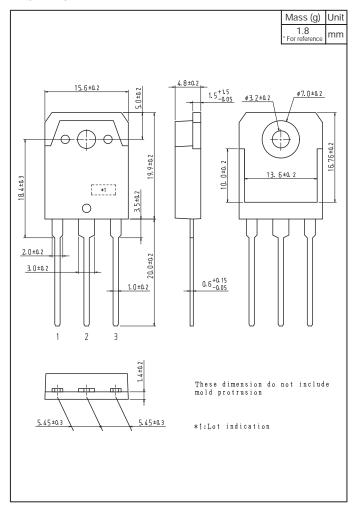


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase			
LEAD FREE	3	JEITA Phase 3A			

Outline Drawing

2SK4125-1E



Note on usage: Since the 2SK4125 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

- Any and all SANYO Semiconductor Co.,Ltd. products described or contained herein are, with regard to "standard application", intended for the use as general electronics equipment. The products mentioned herein shall not be intended for use for any "special application" (medical equipment whose purpose is to sustain life, aerospace instrument, nuclear control device, burning appliances, transportation machine, traffic signal system, safety equipment etc.) that shall require extremely high level of reliability and can directly threaten human lives in case of failure or malfunction of the product or may cause harm to human bodies, nor shall they grant any guarantee thereof. If you should intend to use our products for new introduction or other application different from current conditions on the usage of automotive device, communication device, office equipment, industrial equipment etc., please consult with us about usage condition (temperature, operation time etc.) prior to the intended use. If there is no consultation or inquiry before the intended use, our customer shall be solely responsible for the use.
- Specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- SANYO Semiconductor Co.,Ltd. assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein.
- Regarding monolithic semiconductors, if you should intend to use this IC continuously under high temperature, high current, high voltage, or drastic temperature change, even if it is used within the range of absolute maximum ratings or operating conditions, there is a possibility of decrease reliability. Please contact us for a confirmation.
- SANYO Semiconductor Co.,Ltd. strives to supply high-quality high-reliability products, however, any and all semiconductor products fail or malfunction with some probability. It is possible that these probabilistic failures or malfunction could give rise to accidents or events that could endanger human lives, trouble that could give rise to smoke or fire, or accidents that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO Semiconductor Co.,Ltd. products described or contained herein are controlled under any of applicable local export control laws and regulations, such products may require the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written consent of SANYO Semiconductor Co.,Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor Co.,Ltd. product that you intend to use.
- Upon using the technical information or products described herein, neither warranty nor license shall be granted with regard to intellectual property rights or any other rights of SANYO Semiconductor Co.,Ltd. or any third party. SANYO Semiconductor Co.,Ltd. shall not be liable for any claim or suits with regard to a third party's intellectual property rights which has resulted from the use of the technical information and products mentioned above.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.